

UTC UNISONIC TECHNOLOGIES CO., LTD

CR03AM-12 **SCR**

THYRISTOR

DESCRIPTION

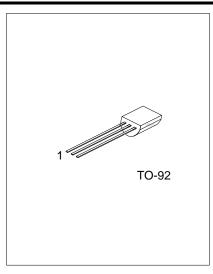
The UTC CR03AM-12 is suitable for low power applications.

FEATURES

* $I_{T (AV)} : 0.3 A$ * V_{DRM}: 600 V * I_{GT} : 100 μA

* Non-Insulated Type

* Glass Passivation Type



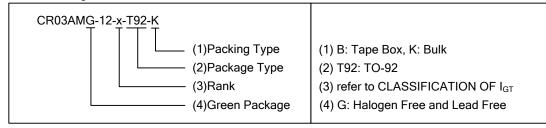
SYMBOL



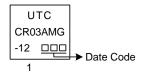
ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			De abia a	
		1	2	3	Packing	
CR03AMG-12-x-T92-B	TO-92	G	Α	K	Tape Box	
CR03AMG-12-x-T92-K	TO-92	G	Α	K	Bulk	

Note: Pin assignment: G: Gate A: Anode K: Cathode



MARKING



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■ ABSOLUTE MAXIMUM RATING

PARAMETER		SYMBOL	RATINGS	UNIT
Depatitive Deals Valtage	Reverse	V_{RRM}	600	V
Repetitive Peak Voltage	Off-State (Note2)	V_{DRM}	600	V
Non Depatitive Deals Valtage	Reverse	V_{RSM}	800	V
Non-Repetitive Peak Voltage	Off-State (Note2)	V_{DSM}	800	V
DC Voltage	Reverse	$V_{R(DC)}$	480	V
DC Voltage	Off-State (Note2)	$V_{D(DC)}$	480	V
Dook Cata Valtaga	Forward	V_{FGM}	6	V
Peak Gate Voltage	Reverse	V_{RGM}	6	V
Peak Gate Forward Current		I_{FGM}	0.3	Α
RMS On-State Current		I _{T (RMS)}	0.47	Α
Surge On-State Current (60Hz sine half wave 1 full cycle, peak value, non-repetitive)		I _{TSM}	20	Α
Average On-State Current (Commercial frequency, sine half wave 180° conduction, $T_A = 47^{\circ}$ C)		I _{T(AV)}	0.3	А
I ² t for Fusing (Value corresponding to 1 cycle of half wave 60Hz, surge on-state current)		l ² t	1.6	A ² s
Peak Gate Power Dissipation		P_GM	0.5	W
Average Gate Power Dissipation		$P_{G(AV)}$	0.1	W
Mass (Typical value)			0.23	g
Junction Temperature		T_J	-40 ~ +110	°C
Storage Temperature		T_{STG}	-40 ~ +125	°C
			_	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied

■ THERMAL DATA

PARAMETER	SYMBOL	MAX	UNIT
Junction to Ambient	θ_{JA}	180	°C/W

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Repetitive Peak Reverse Current	I _{RRM}	T _J = 110°C, V _{RRM} applied			0.1	mA
Repetitive Peak Off-State Current	I _{DRM}	T_{J} = 110°C, V_{DRM} applied, R_{GK} =1k Ω			0.1	mA
On-State Voltage (T _A = 25°C)	V_{TM}	I _{TM} = 4 A, instantaneous value			1.8	V
Gate Trigger Voltage	V_{GT}	T_{J} = 25°C, V_{D} =6 V, I_{T} = 0.1A			0.8	V
Gate Non-Trigger Voltage	$V_{\sf GD}$	T_J = 110°C, V_D =1/2 V_{DRM} , R_{GK} =1k Ω	0.2			V
Gate Trigger Current	I_{GT}	$T_J = 25$ °C, $V_D = 6$ V, $I_T = 0.1$ A	1		100	μΑ
Holding Current	I _H	$T_J=25$ °C, $V_D=12$ V, $R_{GK}=1$ k Ω		1.5	3	mA

CLASSIFICATION OF I_{GT}

If special values of I_{GT} are required, choose item D or E from those listed in the table below if possible.

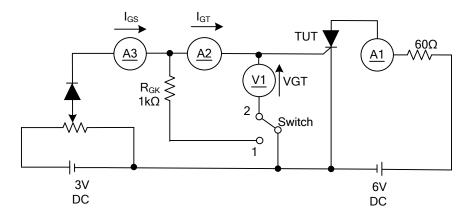
RANK	D	E
RANGE	1 ~ 50	20 ~100

Note: The above values do not include the current flowing through the $1k\Omega$ resistance between the gate and cathode.

^{2.} With gate to cathode resistance $R_{\text{GK}}\!\!=$ $1k\Omega$

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■ I_{GT}, V_{GT} MEASUREMENT CIRCUIT



Switch 1: I_{GT} Measurement Switch 2: V_{GT} Measurement

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